

# N-Channel 30-V (D-S) MOSFET

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| PRODUCT SUMMARY     |                                  |                                 |                       |  |  |
|---------------------|----------------------------------|---------------------------------|-----------------------|--|--|
| V <sub>DS</sub> (V) | $R_{DS(on)}$ ( $\Omega$ )        | I <sub>D</sub> (A) <sup>a</sup> | Q <sub>g</sub> (Typ.) |  |  |
| 30                  | 0.023 at V <sub>GS</sub> = 10 V  | 5.6                             | 2.9 nC                |  |  |
| 30                  | 0.025 at V <sub>GS</sub> = 4.5 V | 4.6                             | 2.9110                |  |  |

#### **FEATURES**

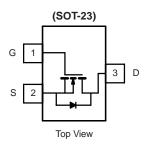
- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

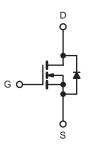


ROHS

### **APPLICATIONS**

DC/DC Converter





N-Channel MOSFET

| <b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25  ^{\circ}C$ , Parameter |   | Symbol                            | Limit  | Unit |  |
|---|---|-----------------------------------|--|------|--|
| Drain-Source Voltage  |   | V <sub>DS</sub>                   | 30   | V    |  |
| Gate-Source Voltage   |   | $V_{GS}$                          | ± 20   |      |  |
| Continuous Drain Current (T <sub>J</sub> = 150 °C)                | $T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$ | I <sub>D</sub>                    | 5.6 <sup>a</sup> 4.3 3.3 2.7                             | A    |  |
| Pulsed Drain Current  |   | I <sub>DM</sub>                   | 17   |      |  |
| Continuous Source-Drain Diode Current                             | $T_C = 25 ^{\circ}C$<br>$T_A = 25 ^{\circ}C$  | I <sub>S</sub>                    | 1.9<br>0.9 <sup>b, c</sup>                               |      |  |
| Maximum Power Dissipation   |   | P <sub>D</sub>                    | 1.8<br>1.2<br>1.1 <sup>b, c</sup><br>0.7 <sup>b, c</sup> | w    |  |
| Operating Junction and Storage Temperature Range                  |   | T <sub>J</sub> , T <sub>stg</sub> | - 55 to 150  | °C   |  |
| Soldering Recommendations (Peak Temperature) <sup>d, e</sup>      |   |                                   | 260  |      |  |

| THERMAL RESISTANCE RATINGS                  |              |            |         |         |      |  |
|---|--------------|------------|---------|---------|------|--|
| Parameter                                   |              | Symbol     | Typical | Maximum | Unit |  |
| Maximum Junction-to-Ambient <sup>b, d</sup> | t ≤ 5 s      | $R_{thJA}$ | 90      | 119     | °C/W |  |
| Maximum Junction-to-Foot (Drain)            | Steady State | $R_{thJF}$ | 60      | 78      | 0/11 |  |

#### Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. Maximum under steady state conditions is 130 °C/W.



| Parameter                                     | Symbol   | Test Conditions   | Min. | Тур.  | Max.  | Unit  |
|---|--|---|------|-------|-------|-------|
| Static  |  |   |      |       |       |       |
| Drain-Source Breakdown Voltage                | $V_{DS}$ $V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$ |   | 30   |       |       | V     |
| V <sub>DS</sub> Temperature Coefficient       |  |   |      | 31    |       | mV/°C |
| V <sub>GS(th)</sub> Temperature Coefficient   | $\Delta V_{GS(th)}/T_J$                                    | 1D = 230 μΑ   |      | - 5   |       | mv/°C |
| Gate-Source Threshold Voltage                 | V <sub>GS(th)</sub>  | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$   | 0.5  |       | 1.5   | V     |
| Gate-Source Leakage                           | I <sub>GSS</sub>   | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$   |      |       | ± 100 | nA    |
| Zana Oata Valta va Busia Oamaat               | I <sub>DSS</sub>   | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V   |      |       | 1     |       |
| Zero Gate Voltage Drain Current               |  | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$                  |      |       | 10    | μA    |
| On-State Drain Current <sup>a</sup>           | I <sub>D(on)</sub>   | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$   | 10   |       |       | Α     |
|   |  | $V_{GS} = 10 \text{ V}, I_D = 3.2 \text{ A}$  |      | 0.023 | 0.026 | Ω     |
| Drain-Source On-State Resistance <sup>a</sup> | R <sub>DS(on)</sub>  | $V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$   |      | 0.025 | 0.028 |       |
| Forward Transconductance <sup>a</sup>         | 9 <sub>fs</sub>  | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.8 A  |      | 12    |       | S     |
| Dynamic <sup>b</sup>                          |  |   |      |       | l     |       |
| Input Capacitance                             | C <sub>iss</sub>   |   |      | 275   |       |       |
| Output Capacitance                            | C <sub>oss</sub>   | $V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$                            |      | 47    |       | pF    |
| Reverse Transfer Capacitance                  | C <sub>rss</sub>   |   |      | 19    |       |       |
| · ·   |  | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.4 A                      |      | 4.5   | 6.7   | nC    |
| Total Gate Charge                             | Q <sub>g</sub> Q <sub>gs</sub>                             | 20 1 00 1 2   |      | 2.1   | 3.2   |       |
| Gate-Source Charge                            |  | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 3.4 \text{ A}$                      |      | 0.85  |       |       |
| Gate-Drain Charge                             | Q <sub>gd</sub>  |   |      | 0.65  |       |       |
| Gate Resistance                               |  |   | 0.8  | 4.4   | 8.8   | Ω     |
| Turn-On Delay Time                            | t <sub>d(on)</sub>   |   |      | 12    | 20    |       |
| Rise Time                                     | t <sub>r</sub>   | $V_{DD} = 15 \text{ V}, R_1 = 5.6 \Omega$   |      | 50    | 75    |       |
| Turn-Off Delay Time                           | t <sub>d(off)</sub>  | $I_D \cong 2.7 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$                          |      | 12    | 20    |       |
| Fall Time                                     | t <sub>f</sub>   |   |      | 22    | 35    |       |
| Turn-On Delay Time                            | t <sub>d(on)</sub>   |   |      | 5     | 10    | ns    |
| Rise Time                                     | t <sub>r</sub>   | $V_{DD} = 15 \text{ V}, R_{L} = 5.6 \Omega$   |      | 12    | 20    | 1     |
| Turn-Off Delay Time                           | t <sub>d(off)</sub>  | $I_D \cong 2.7 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$                           |      | 10    | 15    | -     |
| Fall Time                                     | t <sub>f</sub>   | ()  |      | 5     | 10    | 1     |
| <b>Drain-Source Body Diode Characteristic</b> | · · ·  |   |      |       | 1     |       |
| Continuous Source-Drain Diode Current         | Is   | T <sub>C</sub> = 25 °C  |      |       | 1.9   |       |
| Pulse Diode Forward Current I <sub>SM</sub>   |  |   |      |       | 17    | A     |
| Body Diode Voltage                            | V <sub>SD</sub>  | $I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$   |      | 0.8   | 1.2   | V     |
| Body Diode Reverse Recovery Time              | t <sub>rr</sub>  |   |      | 10    | 20    | ns    |
| Body Diode Reverse Recovery Charge            | Q <sub>rr</sub>  | 1 07 A 11/1 400 A/ T 67 00  |      | 5     | 10    | nC    |
| Reverse Recovery Fall Time                    | t <sub>a</sub>   | $I_F = 2.7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$ |      | 6     |       | ns    |
| Reverse Recovery Rise Time                    | t <sub>b</sub>   |   |      | 4     |       |       |

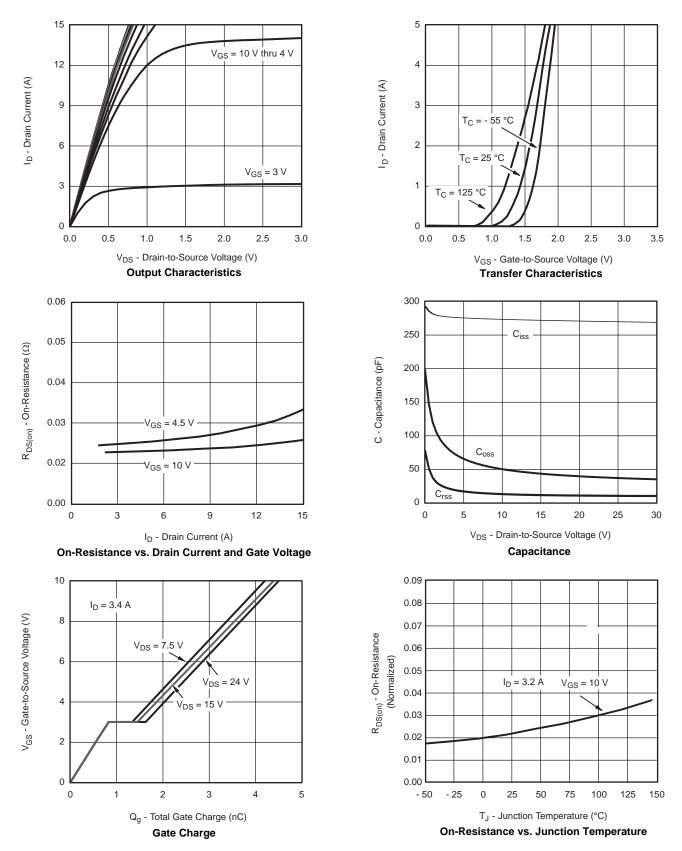
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

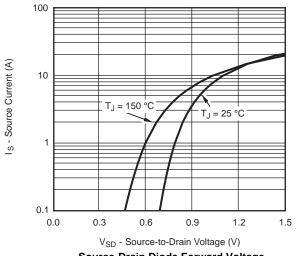


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

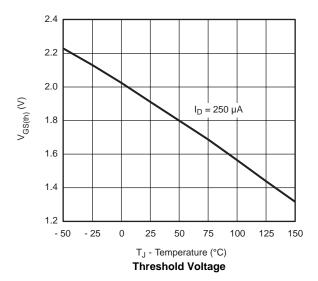


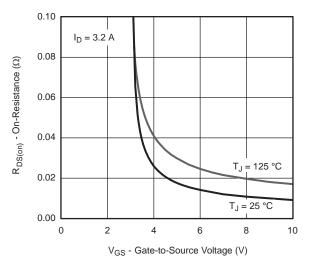


### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



#### Source-Drain Diode Forward Voltage

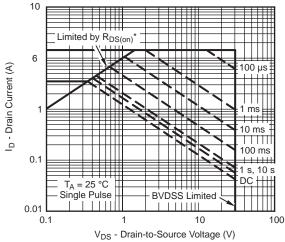




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power

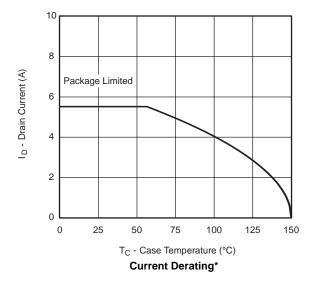


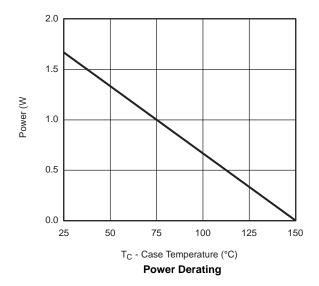
\*  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

Safe Operating Area, Junction-to-Ambient



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

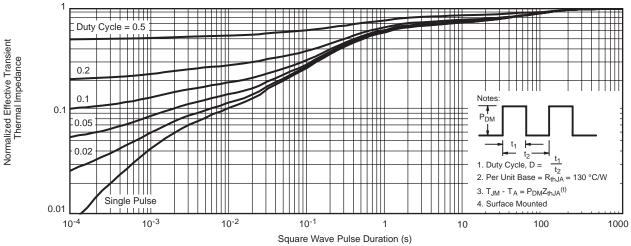




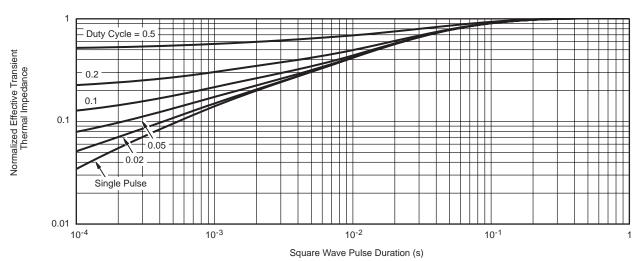
<sup>\*</sup> The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

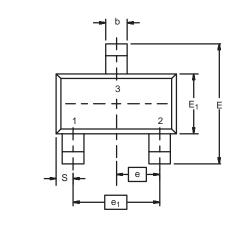


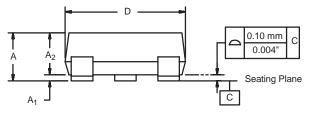
Normalized Thermal Transient Impedance, Junction-to-Foot

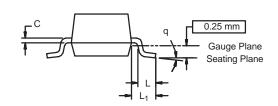
6 Ver.A2



### SOT-23 (TO-236): 3-LEAD





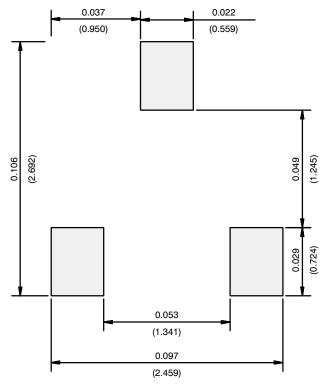


| Dim -          | MILLIM   | IETERS | INCHES     |            |  |  |
|----------------|----------|--------|------------|------------|--|--|
|                | Min      | Max    | Min        | Max        |  |  |
| Α              | 0.89     | 1.12   | 0.035      | 0.044      |  |  |
| A <sub>1</sub> | 0.01     | 0.10   | 0.0004     | 0.004      |  |  |
| A <sub>2</sub> | 0.88     | 1.02   | 0.0346     | 0.040      |  |  |
| b              | 0.35     | 0.50   | 0.014      | 0.020      |  |  |
| С              | 0.085    | 0.18   | 0.003      | 0.007      |  |  |
| D              | 2.80     | 3.04   | 0.110      | 0.120      |  |  |
| E              | 2.10     | 2.64   | 0.083      | 0.104      |  |  |
| E <sub>1</sub> | 1.20     | 1.40   | 0.047      | 0.055      |  |  |
| е              | 0.95 BSC |        | 0.0374 Ref |            |  |  |
| e <sub>1</sub> | 1.90 BSC |        | 0.074      | 0.0748 Ref |  |  |
| L              | 0.40     | 0.60   | 0.016      | 0.024      |  |  |
| L <sub>1</sub> | 0.64 Ref |        | 0.025 Ref  |            |  |  |
| S              | 0.50 Ref |        | 0.020      | Ref        |  |  |
| q              | 3°       | 8°     | 3°         | 8°         |  |  |

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)





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